

	Document ID	Issue Date	Pages	Title
1	US 6455337 B1	20020924	10	Group III-V nitride laser devices with cladding layers to suppress defects such as cracking
2	US 6441393 B2	20020827	8	Semiconductor devices with selectively doped III-V nitride layers
3	US 6345063 B1	20020205	14	Algainn elog led and laser diode structures for pure blue or green emission
4	US 6266355 B1	20010724	10	Group III-V nitride laser devices with cladding layers to suppress defects such as cracking
5	US 6232623 B1	20010515	14	Semiconductor device on a sapphire substrate
6	US 6072197 A	20000606	42	Semiconductor light emitting device with an active layer made of semiconductor having uniaxial anisotropy
7	US 6040588 A	20000321	11	Semiconductor light-emitting device
8	US 5661074 A	19970826	15	High brightness electroluminescent device emitting in the green to ultraviolet spectrum and method of making the same
9	JP 11243251 A	19990907	12	SEMICONDUCTOR LASER

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	298	((light adj emitting adj (diode device)) laser) and Gan and (gainn ingan) and (quantum adj well)	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/10/07 09:40